TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT3S08T

VHF~UHF Band Low Noise Amplifier Applications

Unit: mm

- Sutable for use in an OSC
- Low noise figure

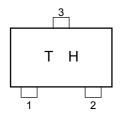
NF = 1.4dB

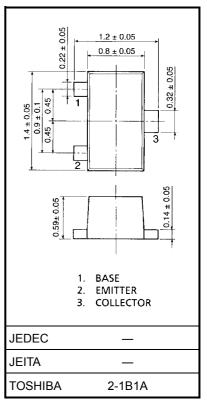
 $|S21e|^2 = 10.5dB$ (@1 V/5 mA/1 GHz)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	20	V
Collector-emitter voltage	V _{CEO}	8	V
Emitter-base voltage	V _{EBO}	1.5	V
Collector current	IC	40	mA
Base current	ΙΒ	10	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	Tstg	-55~125	°C

Marking





Weight: g (typ.)

Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f _T	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}$	2	4.5	_	GHz
Insertion gain	S21e ² (1)	$V_{CE} = 1 \text{ V}, I_C = 5 \text{ mA}, f = 1 \text{ GHz}$		10.5		dB
	S21e ² (2)	$V_{CE} = 3 \text{ V}, I_{C} = 20 \text{ mA}, f = 1 \text{ GHz}$	10.5	13.5		
Noise figure	NF	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	_	1.4	2.5	dB

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 10 \text{ V}, I_{E} = 0$	_	_	0.1	μА
Emitter cut-off current	I _{EBO}	$V_{EB} = 1 \text{ V, } I_{C} = 0$	_	_	1	μΑ
DC current gain	h _{FE}	V _{CE} = 1 V, I _C = 5 mA	80	_	140	_
Reverse transfer capacitance	C _{re}	$V_{CB} = 1 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ (Note)	_	0.55	0.95	pF

Note: C_{re} is measured by 3 terminal method with capacitance bridge.

Caution

This device electrostatic sensitivity. Please handle with caution.

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